

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	1115	(257/E21.548).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/03/17 09:42
S1	1848080	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 07:38
S2	15461	semiconductor with island	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:53
S3	173	semiconductor with island with recess	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:53
S4	3	S3 underetching	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:55
S5	92	S3 etching	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:55
S6	0	S5 high adj ohmic material	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:56
S7	1711	high adj ohm\$ material	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:56
S8	755	S7 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:56
S9	0	S7 S3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:56

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S10	0	S3 high adj ohm\$ material	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:57
S11	31	S7 semiconductor near6 island	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 12:58
S12	755	(high adj ohm\$ material) semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:00
S13	0	(high adj ohm\$ material) semiconductor with island near15 recess	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:00
S14	25	(high adj ohm\$ material) semiconductor near15 recess	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:04
S15	346	(high adj ohm\$ material) semiconductor etch\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:05
S16	15	(high adj ohm\$ material) semiconductor underetch\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:07
S17	15	high adj ohm\$ semiconductor underetch\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:11
S18	4	"6285057"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 15:55
S19	4	"2003045119"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:15

## EAST Search History

S20	13	wang hsiao adj lei	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:29
S21	15	"3715232"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 13:29
S22	41	"5972758"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/16 15:56
S23	43930	semiconductor with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 07:38
S24	6707	semiconductor with trench with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 07:38
S25	120	semiconductor with trench with dielectric with groove	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 07:46
S26	3	semiconductor with trench with dielectric with groove with high adj conductiv\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 08:07
S27	20162	semiconductor with silicon with germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 08:07
S28	15255	semiconductor with (silicon with germanium layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 08:08
S29	516	semiconductor with (mixed crystal with silicon with germanium layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 08:08

## EAST Search History

S30	386	semiconductor with (mixed crystal with silicon with germanium layer) with germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 08:08
S31	3	semiconductor with (mixed crystal with silicon with germanium layer) with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:17
S32	1	semiconductor with (mixed crystal with silicon with germanium layer) with groove	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:43
S33	283	semiconductor with multiple devices with groove	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:44
S34	0	semiconductor with (mixed crystal with silicon with germanium layer) with multiple devices with groove	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:43
S35	64	semiconductor with multiple devices with groove and anisotropic etching	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:45
S36	901649	semiconductor with multiple devices with groove or cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:51
S37	137	semiconductor with multiple devices with groove and cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2007/08/17 12:53
S38	6611500	trench or groove or via or hole	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/03 07:28
S39	7054644	trench or groove or via or hole or cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/03 07:42

## EAST Search History

S42	3	dielectric same sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/03 08:52
S43	160	dielectric same layer	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/03 08:52
S44	7057061	trench or groove or via or hole or cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/04 09:06
S45	160	dielectric same layer	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/04 09:06
S46	110	S44 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/04 09:06
S48	12	"3715232"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 11:58
S49	48	"040280"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 12:09
S50	178	semiconductor with island with recess	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 13:12
S51	19712	(recess or trench) same dielectric same fill\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:45
S52	12187	(recess or trench) with dielectric with fill\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:49

## EAST Search History

S53	16800	(via or recess or trench) with dielectric with fill\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:50
S54	4100	S52 and walls	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:51
S55	18923	(cavity or via or recess or trench) with dielectric with fill\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:53
S56	6453	S55 and walls	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:53
S57	1928	S56 and body	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:53
S58	330	S57 and island	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:54
S59	95	S58 and groove	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/11 14:55
S60	1304	438/758.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 09:26
S61	833	S60 and (recess or trench or groove or via)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 09:26
S64	1689	257/330.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 10:38

## EAST Search History

S65	2476	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 11:49
S66	190	438/412.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 11:59
S67	2161	438/424.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 12:00
S68	18923	(cavity or via or recess or trench) with dielectric with fill\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 12:56
S69	13	S66 and S68	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/12 12:56
S70	3670	(cavity or via or recess or trench) with dielectric with fill\$3.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:09
S71	5	recess with dielectric adj layer with island.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:12
S72	0	recess with dielectric adj layer with underetch with island.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:16
S73	1	recess with dielectric adj layer with fill\$3 with island.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:23
S74	190	438/412.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:24

## EAST Search History

S75	0	recess with dielectric adj layer with fill\$3 with island and S74	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:24
S76	2	recess with dielectric adj layer and S74	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:25
S77	186	438/422.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	AND	ON	2008/03/13 12:25